SLLS534B - MAY 2002 - REVISED OCTOBER 2004

20 PWRDOWN

19 🛛 V_{CC}

18 GND

16 **R**IN1

14 NC

13 DIN1

12 DIN2

11 NC

17 DOUT1

15 **ROUT1**

•	Operates	With 3	3-V to	5.5-V	V _{CC}	Supply	
---	----------	--------	--------	-------	-----------------	--------	--

- Operates Up To 1 Mbit/s
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 \times 0.1 μ F

description/ordering information

- Accepts 5-V Logic Input With 3.3-V Supply
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
 - Applications
 Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment

NC - No internal connection

DB, DW, OR PW PACKAGE (TOP VIEW)

EN 1 C1+ 2

V+[]3

 $C1 - \Pi 4$

C2+ 15

 $C_2 - \Pi_6$

DOUT2 8

RIN2⁹

ROUT2 10

V-**∏**7

The SN65C3222 and SN75C3222 consist of two line drivers, two line receivers, and a dual charge-pump circuit with \pm 15-kV ESD protection pin to pin (serial-port connection pins, including GND). The devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/µs to 150 V/µs.

The SN65C3222 and SN75C3222 can be placed in the power-down mode by setting $\overline{PWRDOWN}$ low, which draws only 1 μ A from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled, V+ is lowered to V_{CC}, and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting \overline{EN} high.

TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING
		Tube of 25	SN75C3222DW	7500000
	SOIC (DW)	Reel of 2000	SN75C3222DWR	75C3222
−0°C to 70°C	SSOP (DB)	Reel of 2000	SN75C3222DBR	CA3222
	T0000 (DW)	Tube of 70	SN75C3222PW	040000
	TSSOP (PW)	Reel of 2000	SN75C3222PWR	CA3222
		Tube of 25	SN65C3222DW	0500000
	SOIC (DW)	Reel of 2000	SN65C3222DWR	65C3222
–40°C to 85°C	SSOP (DB)	Reel of 2000	SN65C3222DBR	CB3222
		Tube of 70	SN65C3222PW	00000
	TSSOP (PW)	Reel of 2000	SN65C3222PWR	CB3222

ORDERING INFORMATION

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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Function Tables

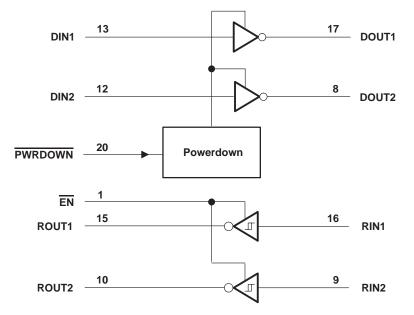
EACH DRIVER						
INF	INPUTS					
DIN	PWRDOWN	DOUT				
Х	L	Z				
L	Н	Н				
Н	Н	L				

H = high level, L = low level, X = irrelevant, Z = high impedance

EACH RECEIVER						
INPU	JTS	OUTPUT				
RIN	EN	ROUT				
L	L	Н				
Н	L	L				
Х	Н	Z				
Open	L	Н				

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} (see Note 1)	
Positive output supply voltage range, V+ (see Note 1)	
Negative output supply voltage range, V– (see Note 1) Supply voltage difference, V+ – V– (see Note 1)	
Input voltage range, V_{I} : Drivers, \overline{EN} , $\overline{PWRDOWN}$	
Receivers	
Output voltage range, V _O : Drivers	
Receivers	
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DB package	
DW package	58°C/W
PW package	83°C/W
Operating virtual junction temperature, T _J	150°C
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

- 2. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 5)

				MIN	NOM	MAX	UNIT
	Quantum la re	V _{CC} = 3.3 V		3	3.3	3.6	N/
	Supply voltage	$V_{CC} = 5 V$		4.5	5	5.5	V
			V _{CC} = 3.3 V	2			V
VIH	Driver and control high-level input voltage	DIN, EN, PWRDOWN	$V_{CC} = 5 V$	2.4			V
VIL	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	V
VI	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
VI	Receiver input voltage			-25		25	V
т.	Operating free air temperature	SN65C3222	SN65C3222 SN75C3222			85	°C
TA	Operating free-air temperature	SN75C3222				70	Ĵ

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
Ц	Input leakage current (EN, PWRDOWN)			±0.01	±1	μA
	Supply current	No load, PWRDOWN at V _{CC}		0.3	1	mA
ICC	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μA

[‡] All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



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DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS			TYP†	MAX	UNIT
VOH	High-level output voltage	DOUT at R _L = 3 k Ω to GND,	DIN = GND	5	5.4		V
VOL	Low-level output voltage	DOUT at R _L = 3 k Ω to GND,	$DIN = V_{CC}$	-5	-5.4		V
Iн	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
١ _{IL}	Low-level input current	V _I at GND			±0.01	±1	μΑ
		V _{CC} = 3.6 V,	$V_{O} = 0 V$		±35	±60	
los	Short-circuit output current‡	V _{CC} = 5.5 V,	$V_{O} = 0 V$		±35	±90	mA
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	$V_{O} = \pm 2 V$	300	10M		Ω
1	Output lookago ourrant	PWRDOWN = GND	$V_{O} = \pm 12 \text{ V}, V_{CC} = 3 \text{ V to } 3.6 \text{ V}$			±25	
loff	Output leakage current		$V_{O} = \pm 10$ V, $V_{CC} = 4.5$ V to 5.5 V			±25	μA

[†] All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25^{\circ}$ C.

[‡] Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	-	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
Maximum data rate (see Figure 1)			C _L = 1000 pF		250			
		$R_L = 3 k\Omega$, One DOUT switching	C _L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			kbit/s
		one beer entering	C _L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
^t sk(p)	Pulse skew§	C _L = 150 pF to 2500 pF	$R_L = 3 k\Omega$ to 7 kΩ, See Figure 2			300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	$R_L = 3 k\Omega$ to 7 kΩ, V _{CC} = 3.3 V	$C_{L} = 150 \text{ pF to } 1000$) pF	18		150	V/µs

[†] All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25^{\circ}$ C.

\$ Pulse skew is defined as $|tp_{LH} - tp_{HL}|$ of each channel of the same device. NOTE 4: Test conditions are C1-C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2-C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



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RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
VOH	High-level output voltage	$I_{OH} = -1 \text{ mA}$	V _{CC} – 0.6 V	V _{CC} – 0.1 V		V
VOL	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V		V _{CC} = 3.3 V		1.5	2.4	V
V _{IT+}	Positive-going input threshold voltage	$V_{CC} = 5 V$		1.8	2.4	V
N/		V _{CC} = 3.3 V	0.6	1.2		V
VIT-	Negative-going input threshold voltage	$V_{CC} = 5 V$	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} – V _{IT} _)			0.3		V
loff	Output leakage current	$\overline{EN} = V_{CC}$		±0.05	±10	μΑ
ri	Input resistance	$V_I = \pm 3 V \text{ to } \pm 25 V$	3	5	7	kΩ

[†] All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST CONDITIONS	MIN TYP [†] MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output	$C_{L} = 150 \text{ pF}$, See Figure 3	300	ns
^t PHL	Propagation delay time, high- to low-level output	CL= 150 pF, See Figure 3	300	ns
t _{en}	Output enable time	C_L = 150 pF, R_L = 3 k Ω , See Figure 4	200	ns
^t dis	Output disable time	C_L = 150 pF, R_L = 3 k Ω , See Figure 4	200	ns
^t sk(p)	Pulse skew [‡]	See Figure 3	300	ns

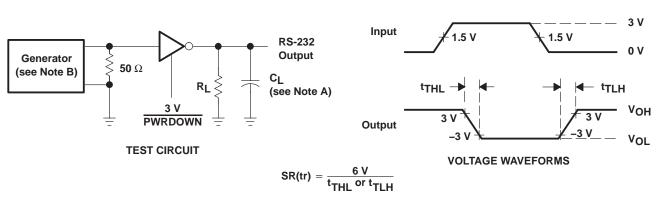
[†] All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25^{\circ}$ C.

[‡]Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



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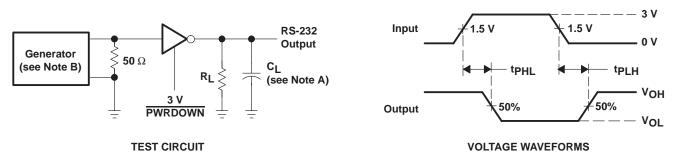


PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

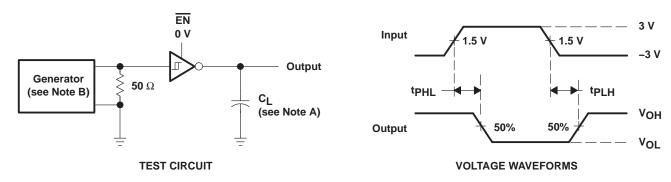
Figure 1. Driver Slew Rate



NOTES: A. CL includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_{O} = 50 Ω , 50% duty cycle, $t_{f} \le 10$ ns. $t_{f} \le 10$ ns.

Figure 2. Driver Pulse Skew

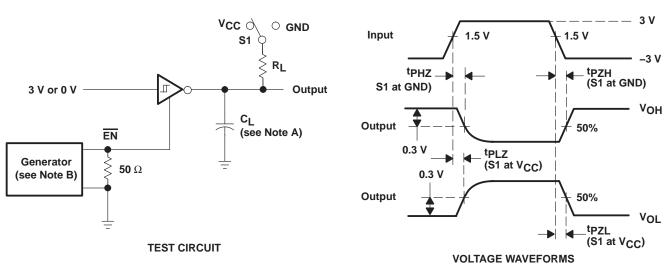


NOTES: A. CL includes probe and jig capacitance. B. The pulse generator has the following characteristics: $Z_{O} = 50 \Omega$, 50% duty cycle, $t_{r} \le 10$ ns, $t_{f} \le 10$ ns.

Figure 3. Receiver Propagation-Delay Times



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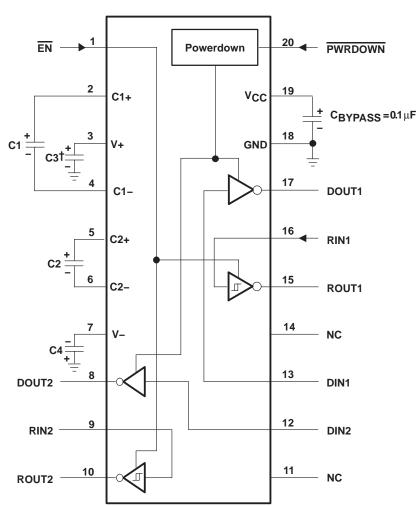
PARAMETER MEASUREMENT INFORMATION



Figure 4. Receiver Enable and Disable Times



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APPLICATION INFORMATION

 $^{\dagger}\,\text{C3}$ can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. NC - No internal connection

v _{cc}	C1	C2, C3, and C4
3.3 V \pm 0.3 V	0.1 μ F	0.1 μF
5 V \pm 0.5 V	0.047 μF	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

V _{CC} vs	CAPACITOR	VALUES
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Figure 5. Typical Operating Circuit and Capacitor Values





PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(1)		g		,	(2)	(6)	(3)		(4/3)	
SN65C3222DBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	Samples
SN65C3222DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222	Samples
SN65C3222PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	Samples
SN65C3222PWR	NRND	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	
SN75C3222DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222DWG4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3222	Samples
SN75C3222PWR	NRND	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3222	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN65C3222PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN75C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75C3222PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

5-Jan-2022



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222DBR	SSOP	DB	20	2000	853.0	449.0	35.0
SN65C3222DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN65C3222PWR	TSSOP	PW	20	2000	853.0	449.0	35.0
SN75C3222DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN75C3222PWR	TSSOP	PW	20	2000	853.0	449.0	35.0



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5-Jan-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN65C3222PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN75C3222DW	DW	SOIC	20	25	507	12.83	5080	6.6
SN75C3222DWG4	DW	SOIC	20	25	507	12.83	5080	6.6
SN75C3222PW	PW	TSSOP	20	70	530	10.2	3600	3.5

PW0020A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



PW0020A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0020A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



LAND PATTERN DATA



NOTES: Α. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
 C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DB0020A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



DB0020A

EXAMPLE BOARD LAYOUT

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DB0020A

EXAMPLE STENCIL DESIGN

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



DW0020A

EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DW0020A

EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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